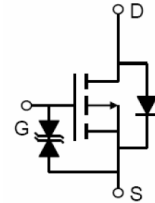


Trench P-Channel PowerMOSFET Wafer Datasheet

FEATURES

- -150V、40A* , P-channel
- $R_{DS(on)} = 70m\Omega(MAX)$
- Ultra low Q_{gd}
- Fast switching

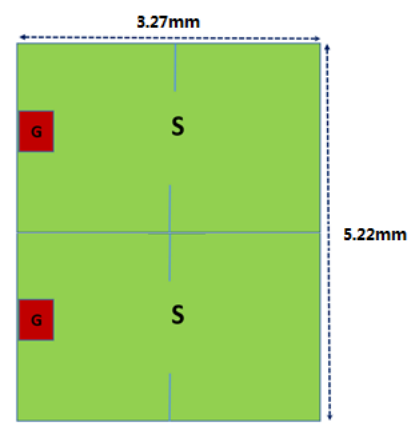


Schematic diagram

Electrical Characteristics($T_J = 25^\circ C$)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-150			V	$V_{GS} = 0V, I_D = -250\mu A$
$R_{DS(on)}$	Static Drain-Source On-Resistance			70	m Ω	$V_{GS} = 10V, I_D = -20A$
$V_{GS(th)}$	Gate Threshold Voltage	-1.0		-3.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
I_{DSS}	Drain-to-Source Leakage Current			1	μA	$V_{DS} = -145V, V_{GS} = 0V, T_J = 25^\circ C$
I_{GSS}	Gate-Body Leakage Current			± 10	μA	$V_{GS} = \pm 20V$
V_{SD}	Body Diode Voltage			1.5	V	$V_{GS} = 0V, I_{SD} = -40A$
T_J, T_{stg}	Operating and Storage Temperature Range	-55~+150			$^\circ C$	

Mechanical Date

Die Size	3270×5220	μm^2	
Gate Pad Size	300×400*2		
Source Pad Size	No Passivation		
Scribe Line Size	60	μm	
Wafer Diameter	200	mm	
Wafer Thickness	175-200	μm	
Passivation Frontside	No Passivation	---	
Source Metallization	AL	4.0	
Drain Metallization	Ti- Ni - Ag	1.3	
Reject Ink Dot Size	0.51	mm	
Recommended Storage Environment	Store in original container, in dessicated nitrogen, with no contamination		

* Electrical characteristics are reported for the reference packaged part (TO-252/220) and can not be guaranteed in die sales form.

Variations in customer packaging materials, dimensions and processes may affect parametric performance.